

3-TERMINAL 0.3A POSITIVE VOLTAGE REGULATORS

This series of fixed-voltage monolithic integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. In addition, they can be used with power-pass elements to make high current voltage regulators. Each of these regulators can deliver up to 100mA output current.

The internal limiting and thermal shutdown features of these regulators make them essentially immune to overload.

When used as a replacement for a zener diode-resistor combination, an effective improvement in output impedance can be obtained together with lower-bias current.



Features

- Output current Up to 300mA
- No External Components
- Internal Thermal Overload Protection
- Internal Short-Circuit Limiting
- Output Voltage of 5V, 6V, 8V, 9V, 10V, 12V, 15V, 18V and 24V

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Packing
HT78HXXATZ		TO-92	Bulk
HT78HXXARTZ	T 100 / 1070 0	TO-92	Taping
HT78HXXARZ	$1A = -40^{\circ} t0 \ 125^{\circ} C$	SO-8	Tape & Reel
HT78HXXARDZ		SOT-89	Tape & Reel

Pin Configuration



SO-8



SOT-89





Absolute Maximum Ratings

Charac	teristic	Symbol	Value	Unit
	HT78H05 ~ HT78H10		30	
Input voltage	HT78H12 ~ HT78H18	VI	35	V
	HT78H24		40	
	TO-92		625	
Power Dissipation	SOT-89	Pd	500	mW
	SOP-8		625	
Operating junction ter	mperature	Topr	-40 ~ +150	
Storage temperature		Tstg	-65 ~ +150	°C
Soldering temperature	e and time	Tsol	260/10sec	

* Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied.

Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

78	BHxx	Min.	Max.	Unit
	HT78H05	7	20	
	HT78H06	8	20	
	HT78H08	10.5	23	
	HT78H09	11.5	24	
Input voltage, VI	HT78H10	12.5	25	V
	HT78H12	14.5	27	
	HT78H15	17.5	30	
	HT78H18	20.5	33	
	HT78H24	26.5	39	
Output current, lo			300	mA
Operating virtual junction terr	nperature, Tj	-40	125	°C

TYPICAL APPLICATION



Notes

1. To specify an output voltage, substitute voltage for "XX"

2. Bypass capacitors are recommended for optimum stability and transient response and should be located as close as possible to the regulators.



HT78H05 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=10V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
		25°C		4.8	5	5.2	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 7V≤ VI≤ Vmax	-40 ∼ 125°C	4.75	5	5.25	V
		1 mA≤lo≤ 70 mA		4.75	5	5.25	
Line regulation	Realine	7≤ VI≤ 20V	25°C		32	150	m\/
Line regulation	Neg inte	8≤ VI≤ 20V	200		26	100	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		15	60	mV
		1 mA≤ lo≤ 40 mA			8	30	
Bias current	1-		25°C		3.8	6	mΛ
bias current	d		125°C			5.5	III
Piac current change	Als	9≤ VI≤ 20V	40 125°C			1.5	۳۸
bias current change	7'B	1 mA≤ lo≤ 40 mA	-40 ~ 125 0			0.1	IIIA
Output noise voltage	V	10 Hz≤ f≤ 100 kHz	25°C		42		μV
Ripple rejection	RR	8≤ VI≤ 20V f=120 Hz	25℃	41	49		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H06 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=12V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	Test condition *		Тур.	Max.	Unit
			25°C	5.75	6	6.25	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 8V≤ VI≤ 20V	-40 ~ 125℃	5.7	6	6.3	V
		1 mA≤lo≤ 70 mA		5.7	6	6.3	
Line regulation	gulation Beg line 8≤ VI≤ 20V	25°C		35	175	m\/	
Line regulation	Regime	9≤ VI≤ 20V	23.0		29	125	mv
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		16	80	mV
		1 mA≤ lo≤ 40 mA			9	40	
Bios current	1-		25°C		3.9	6	۳۸
bias current	в		125°C			5.5	
Piac current change	Als	9≤ VI≤ 20V	40 125°C			1.5	۳۸
bias current change	7'B	1 mA≤ lo≤ 40 mA	-40 ~ 125 0			0.1	
Output noise voltage	V	10 Hz≤ f≤ 100 kłłz	25℃		46		μV
Ripple rejection	RR	9≤ VI≤ 19V f=120 Hz	25°C	40	48		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H08 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=14V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
			25°C	7.7	8	8.3	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 10.5V≤ VI≤ 23V	-40 ~ 125°C	7.6	8	8.4	V
		1 mA≤lo≤ 70 mA		7.6	8	8.4	
Line regulation	Realine	10.5≤ VI≤ 23V	25°C		42	175	m\/
	Regime	11≤ VI≤ 23V	23.0		36	125	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		18	80	. mV
		1 mA≤ lo≤ 40 mA			10	40	
			25°C		4	6	
Bias current	B		125°C			5.5	mA
Dias ourrent change	<u>Als</u>	11≤ VI≤ 23V	40 125°C			1.5	
bias current change	ΔB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	mA
Output noise voltage	V _N	10 Hz≤ f≤ 100 kłż	25°C		54		μN
Ripple rejection	RR	13≤ VI≤ 23V f=120 Hz	25°C	37	46		dB
Dropout voltage	V		25℃		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H09 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=14V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
			25°C	806	9	9.4	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 12V≤ VI≤ 24V	-40 ~ 125℃	8.55	9	9.45	V
		1 mA≤lo≤ 70 mA		8.55	9	9.45	
Line regulation	Regline	12≤ VI≤ 24V	25°C		45	175	mV
Line regulation	Reg line	13≤ VI≤ 24V	23.0		40	125	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		19	90	. mV
		1 mA≤ lo≤ 40 mA	200		11	40	
			25°C		4.1	6	
Bias current	В		125°C			5.5	mA
Diag ourrent change	<u>Als</u>	13≤ VI≤ 24V	40 125°C			1.5	
bias current change	ΔIB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	mA
Output noise voltage	V _N	10 Hz≤ f≤ 100 kHz	25°C		58		μN
Ripple rejection	RR	13≤ VI≤ 23V f=120 Hz	25°C	38	45		dB
Dropout voltage	V		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H10 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=16V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
			25°C	9.6	10	10.4	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 13V≤ VI≤ 25V	-40 ~ 125℃	9.5	10	10.5	V
		1 mA≤lo≤ 70 mA		9.5 10 1	10.5		
Line regulation	Realine	13≤ VI≤ 25V	25°∩		51	175	mV
Line regulation	Nog into	14≤ VI≤ 25V	200		42	125	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		20	90	. mV
		1 mA≤ lo≤ 40 mA	200		11	40	
	1		25°C		4.2	6	
Bias current	B		125°C			5.5	mA
Pice current change	Ala	14≤ VI≤ 25V	40 125°C			1.5	٣٨
bias current change	ΔB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	mA
Output noise voltage	V _N	10 Hz≤ f≤ 100 kłb	25°C		62		μN
Ripple rejection	RR	15≤ VI≤ 25V f=120 Hz	25°C	37	44		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H12 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=17V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
			25°C	11.5	12	12.5	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 14V≤ VI≤ 27V	-40 ~ 125℃	11.4	12	12.6	V
		1 mA≤lo≤ 70 mA	11.4	11.4	12	12.6	
Line regulation	Realine	14.5≤ VI≤ 27V	25°C		55	250	mV
Line regulation	Regime	16≤ VI≤ 27V	200		49	200	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		22	100	. mV
		1 mA≤ lo≤ 40 mA	200		13	50	
			25°C		4.3	6.5	
Bias current	B		125°C			6	mA
Riac current change	Als	16≤ VI≤ 27V	40 125°C			1.5	m۸
bias current change	ΔB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	ma
Output noise voltage	V _N	10 Hz≤ f≤ 100 kt/z	25°C		70		μN
Ripple rejection	RR	15≤ VI≤ 25V f=120 Hz	25°C	37	42		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H15 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=19V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test condi	tion *	Min	Тур.	Max.	Unit
			25°C	14.4	15	15.6	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 17.5V≤ VI≤ 30V	-40 ~ 125℃	14.25	15	15.75	V
		1 mA≤lo≤ 70 mA		14.25	15	15.75	
Line regulation	Regline	17.5≤ VI≤ 30V	25℃		65	300	mV
	Reg line	19≤ VI≤ 30V	23.0		58	250	IIIV
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		25	150	. mV
		1 mA≤ lo≤ 40 mA	200		15	75	
			25°C		4.2	6.5	
Bias current	В		125°C			6	mA
Bias current change	Als	19≤ VI≤ 30V	40 125°C			1.5	m۸
bias current change	ΔB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	mA
Output noise voltage	V _N	10 Hz≤ f≤ 100 klb	25°C		82		μN
Ripple rejection	RR	18.5≤ VI≤ 28.5V f=120 Hz	25°C	37	44		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H18 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=23V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test cond	ition *	Min	Тур.	Max.	Unit
			25°C	17.3	18	18.7	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 20.5V≤ VI≤ 33V	-40 ~ 125℃	17.1	18	18.9	V
		1 mA≤lo≤ 70 mA		17.1	18	18.9	
Line regulation	Regline	20.5≤ VI≤ 33V	25°C		70	360	mV
Line regulation	Regime	22≤ VI≤ 33V	23 0		64	300	mv
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	∂5°C		27	180	. mV
		1 mA≤ lo≤ 40 mA	23 0		19	90	
			25°C		4.7	6.5	
Bias current	В		125°C			6	mA
Pice current change	<u>Als</u>	22≤ VI≤ 33V	40 125°C			1.5	- mA
bias current change	ΔB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	
Output noise voltage	V _N	10 Hz≤ f≤ 100 kHz	25°C		82		μN
Ripple rejection	RR	21.5≤ VI≤ 31.5V f=120 Hz	25°C	32	36		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible.

Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



HT78H24 ELECTRICAL CHARACTERISTICS

(At specified virtual junction temperature, VI=26V, Io=40mA (unless otherwise noted)

Characteistic	Symbol	Test cond	ition *	Min	Тур.	Max.	Unit
			25°C	23	24	25	
Output voltage **	Vout	1 mA≤ lo≤ 40 mA 26.5V≤ VI≤ 39V	-40 ~ 125℃	22.8	24	25.2	V
		1 mA≤lo≤ 70 mA	lo≤ 70 mA	22.8	24	25.2	
Line regulation	26.5≤ VI≤ 39V	26.5≤ VI≤ 39V	25°C		95	480	m\/
	Regime	29≤ VI≤ 39V	230		78	400	mv
Load regulation	Reg load	1 mA≤ lo≤ 100 mA	25°C		41	240	. mV
Load regulation		1 mA≤ lo≤ 40 mA			28	120	
			25°C		4.8	6.5	
Bias current	В		125°C			6	mA
Pige ourrent change	<u>Als</u>	28≤ VI≤ 39V	40 125°C			1.5	m4
bias current change	ΔIB	1 mA≤ lo≤ 40 mA	-40 ~ 125 C			0.1	mA
Output noise voltage	V _N	10 Hz≤ f≤ 100 kHz	25°C		82		μN
Ripple rejection	RR	27.5≤ VI≤ 37.5V f=120 Hz	25°C	30	33		dB
Dropout voltage	VD		25°C		1.7		V

Notes

*. Pulse testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately.

All characteristics are measured with a 0.33 μ F capacitor across the input and a 0.1 μ F capacitor across the output.



• TO-92





• SO-8



D SUFFIX SOIC (MS - 012AA)



	Dimension, mm	
Symbol	MIN	MAX
Α	4.8	5
В	3.8	4
С	1.35	1.75
D	0.33	0.51
F	0.4	1.27
G	1.27	
Н	5.72	
J	0 °	8 °
K	0.1	0.25
М	0.19	0.25
Р	5.8	6.2
R	0.25	0.5

NOTES:

- 1. Dimensions A and B do not include mold flash or protrusion.
- 2. Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B 0.25 mm (0.010) per side.

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